







# NID<sup>TM</sup> Dry

Drying technology for up to 300mm wafers



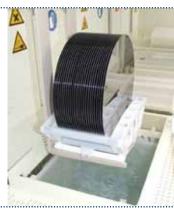
#### **BENEFITS**

**NID** *Dry* stands for Nitrogen IPA Dispense Dry and is a surface tension gradient dryer

Drying technology for up to 300 mm wafers.

- → Stand-alone or integrated in a wet bench
- -> Optimized footprint
- --> Proven technology
- $\rightarrow$  Watermark-free
- --> No wafer breakage





# **FEATURES & BENEFITS**

# **Applications**

Drying of wafers, ICs, MEMS, LED, photo masks, glas substrates

#### **General Features**

- -> Drying of 25 or 50-wafer batches up to 300 mm wafers
- ->> Standard high or low profile cassettes

#### Specification

Process Time: typical < 10 min, depending on selected recipe

Hydrophilic wafers:  $\leq$  10 adders @ 0.12  $\mu$ m Hydrophobic wafers:  $\leq$  30 adders @ 0.12  $\mu$ m

Metal contamination:  $\leq 1 \cdot 10^{10}$  atoms / cm² added for any trace metal

Drying spots: non, after drying

IPA consumtion: ≤ 30 ml / run

Edge exclusion: 3 mm

# **Graphical User Interface**

- → Based on B&R plc
- ightarrow Recipe editor
- → Automatic generation of diagnostic files (EOR, ERR etc.)
- --> Multi-tiered password levels

### General Installation data

Dimensions: 660 x 1440 x 2200 (L x D x H)

Nom. Voltage: 3 x 400 VAC Rated frequency: 50 Hz Nominal current: 3 x 33 A (etc.)

## Available training

Operator, maintenance and process

## Build to comply with

- ---> CE
- $\rightarrow$  Semi S2 and S8
- → FM 4910
- → SECS/GEM

# **Available options**

- $\, \twoheadrightarrow \, \text{Minienvironment}$
- $\Rightarrow$  IPA concentration monitoring system
- → N2 hot
- → UPS unit

# Reliability

- --> MTBF ≥ 800 h
- → MTBA  $\ge 300 \text{ h}$
- --> Uptime ≥ 97 %